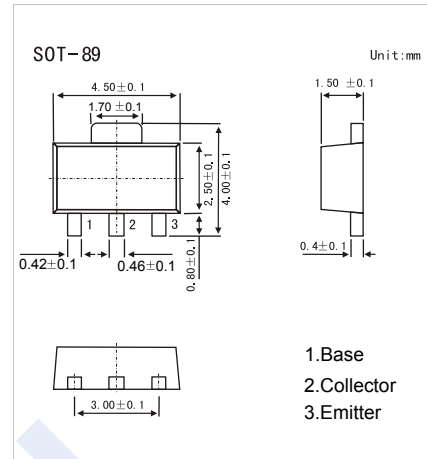
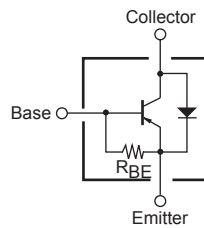


PNP Transistors

2SB1397-HF

■ Features

- Low collector to emitter saturation voltage
- Large current capacity
- Complementary to 2SD2100-HF
- Pb-Free Package May be Available.
The G-Suffix Denotes
Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-25	V
Collector - Emitter Voltage	V_{CE0}	-20	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-2	A
Collector Current - Pulse	I_{CP}	-4	
Collector Power Dissipation	P_C	1.3	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-25			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10 \text{ mA}, R_{BE} = \infty$	-20			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-6			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -20\text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		-0.25	-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$			-1.5	
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -500 \text{ mA}$	70			
		$V_{CE} = -2\text{V}, I_C = -2 \text{ A}$	50			
Base to emitter resistance	R_{BE}				1.6	$\text{k}\Omega$
Diode forward voltage	V_F				-1.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		40		pF
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -500 \text{ mA}$		300		MHz

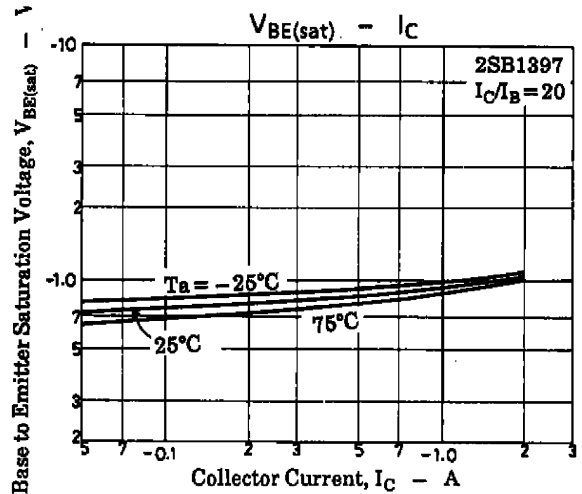
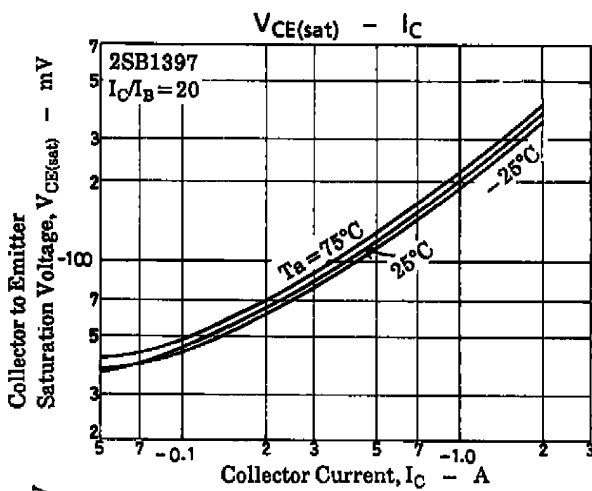
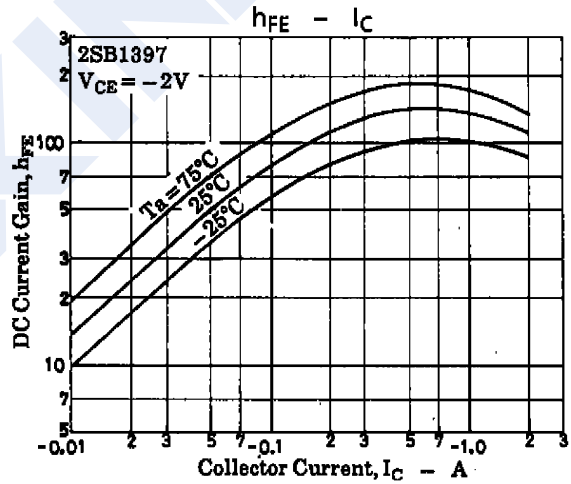
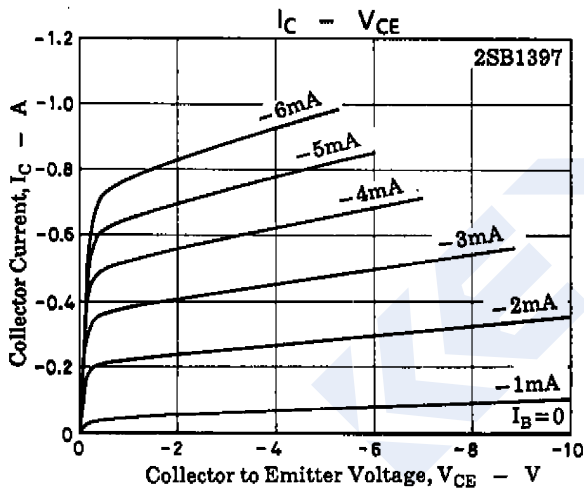
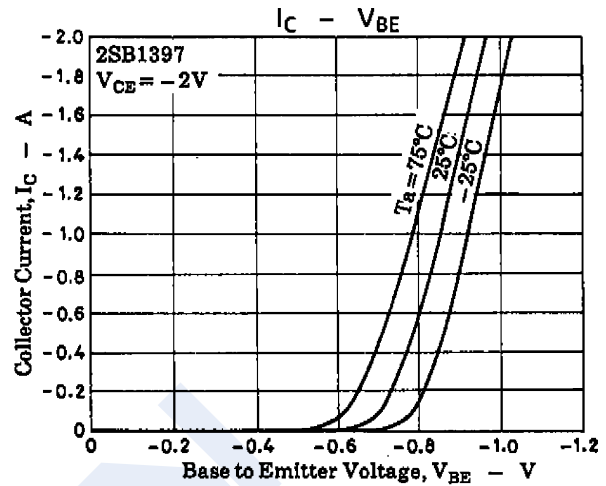
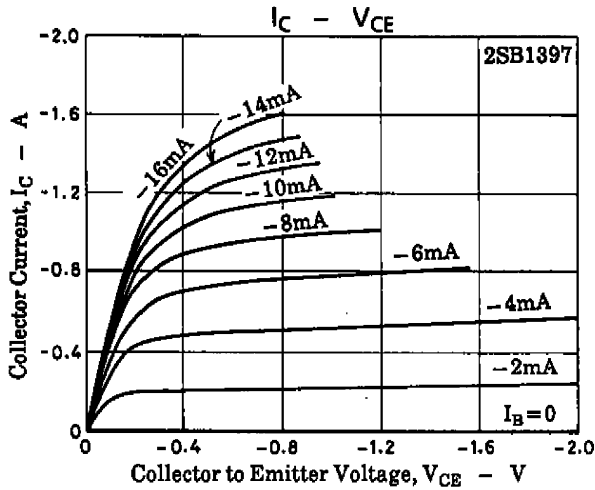
■ Marking

Marking	BP F
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PNP Transistors

2SB1397-HF

■ Typical Characteristics



PNP Transistors

2SB1397-HF

■ Typical Characteristics

